

(010) Principal-Face β -Ga₂O₃ Single Crystals Grown by EFG Method

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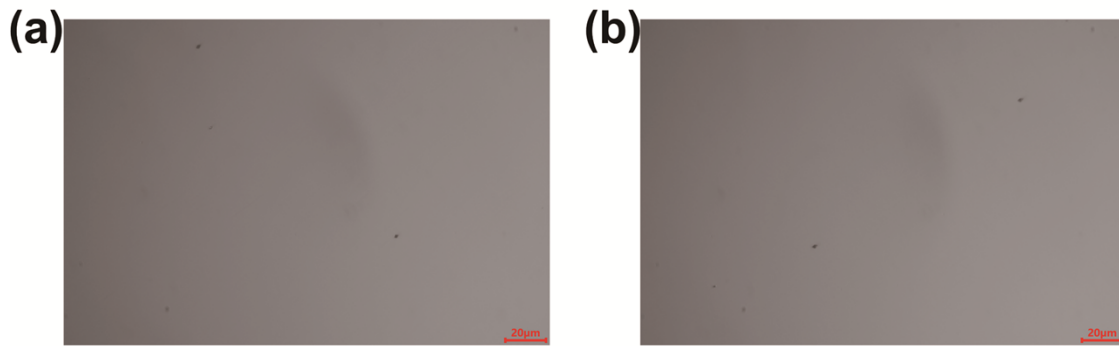


Fig. S1. dislocation-related etch pit density at about 10^3 cm^{-2} level, that revealed by different locations of (a) and (b) for the same (010)-oriented substrate.